

*Attorney docket SAT 200***IN THE CLAIMS**

1. (canceled)

2. (currently amended): The semiconductor apparatus according to claim [[1]] 32, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

3. (currently amended): The semiconductor apparatus according to claim 2, comprising:
a second-conductivity-type area connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,
wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

4. (canceled)

5. (currently amended): The semiconductor apparatus according to claim [[1]] 32, wherein the drain electrode of said first-conductivity-type MOS protection transistor is formed closer to the output electrode than the drain electrode of said first-conductivity-type MOS output transistor.

6. (currently amended): The semiconductor apparatus according to claim [[1]] 32, wherein said first-conductivity-type MOS protection transistor is higher in electrostatic destruction withstanding voltage than said first-conductivity-type MOS output transistor.

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7. (original): The semiconductor apparatus according to claim 6, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

8. (currently amended): The semiconductor apparatus according to claim 7, comprising:

a second-conductivity-type area connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

9. (currently amended): The semiconductor apparatus according to claim 6, wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected by an electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

10. (currently amended): The semiconductor apparatus according to claim 6, wherein the drain electrode of said first-conductivity-type MOS protection transistor is formed closer to the output electrode than the drain electrode of said first-conductivity-type MOS output transistor.

11. (original): The semiconductor apparatus according to claim 10, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

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12. (currently amended): The semiconductor apparatus according to claim 11, comprising:
a second-conductivity-type area connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,
wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.
13. (currently amended): The semiconductor apparatus according to claim 10, wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected by an electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.
14. (original): The semiconductor apparatus according to claim 13, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.
15. (currently amended): The semiconductor apparatus according to claim 14, comprising:
a second-conductivity-type area connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,
wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.
16. (original): A semiconductor apparatus which protects a first-conductivity-type MOS output transistor and a second-conductivity-type MOS output transistor against a surge entering through an output electrode connected to each of drains of said first-conductivity-type MOS output

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transistor whose source is connected to ground and said second-conductivity-type MOS output transistor whose source is connected to a power supply, said apparatus comprising:

a first-conductivity-type MOS protection transistor having a drain connected to the drain of said first-conductivity-type MOS output transistor, a source connected to a source of said first-conductivity-type MOS output transistor, and a gate connected to a second-conductivity-type layer under a gate of said first-conductivity-type MOS output transistor; and

a second-conductivity-type MOS protection transistor having a drain connected to the drain of said second-conductivity-type MOS output transistor, a source connected to a source of said second-conductivity-type MOS output transistor, and a gate connected to a first-conductivity-type layer under a gate of said second-conductivity-type MOS output transistor.

17. (original): The semiconductor apparatus according to claim 16, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

18. (original): The semiconductor apparatus according to claim 17, comprising:

a second-conductivity-type area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

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19. (original): The semiconductor apparatus according to claim 16, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.
20. (original): The semiconductor apparatus according to claim 16, wherein the drains of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are formed closer to the output electrode than the drains of said first-conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.
21. (original): The semiconductor apparatus according to claim 16, wherein said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are higher in electrostatic destruction withstand voltage than said first-conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.
22. (original): The semiconductor apparatus according to claim 21, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.
23. (original): The semiconductor apparatus according to claim 22, comprising:
- a second-conductivity-type area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and
 - a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,
- wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

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wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

24. (original): The semiconductor apparatus according to claim 21, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

25. (original): The semiconductor apparatus according to claim 21, wherein the drains of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are formed closer to the output electrode than the drains of said first-conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.

26. (original): The semiconductor apparatus according to claim 25, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

27. (original): The semiconductor apparatus according to claim 26, comprising:

a second-conductivity-type area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

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wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

28. (original): The semiconductor apparatus according to claim 25, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

29. (original): The semiconductor apparatus according to claim 28, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

30. (original): The semiconductor apparatus according to claim 29, comprising:

a second-conductivity-type area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

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31. (currently amended): The semiconductor apparatus according to claim ~~[[1]]~~ 32, wherein the gate electrode of said first-conductivity-type MOS protection transistor is directly connected by the electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

32. (new): A semiconductor apparatus comprising:

an output electrode from which an output signal of the semiconductor apparatus is output;

a first-conductivity-type MOS output transistor respectively including a drain electrode connected to the output electrode, a source electrode connected to a ground voltage terminal, a gate electrode connected to a signal line, and a second-conductivity-type layer located under the gate electrode, wherein the first-conductivity-type MOS output transistor transmits the output signal of the semiconductor apparatus to the output electrode responsive to a signal on the signal line;

a first-conductivity-type MOS protection transistor respectively including a drain electrode connected to the output electrode, a source electrode connected to the ground voltage terminal, and a gate electrode connected to the ground voltage terminal; and

a metallic wiring member which connects the second-conductivity-type layer of the first-conductivity-type MOS output transistor to the gate electrode of the first-conductivity-type MOS protection transistor.

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